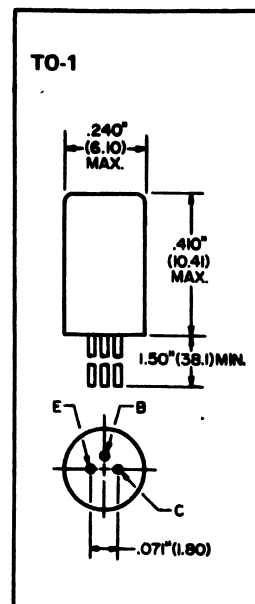


2N200
P-N-P GERMANIUM TRANSISTOR

Transistor Outline



*absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Collector-Base Voltage	25 v
Emitter-Base Voltage	25 v
Collector Current	300 ma
Total Device Dissipation at (or below) 25°C	150 mw
Operating Collector Junction Temperature .	85°C
Storage Temperature Range	-65°C to 100°C

electrical characteristics at 25°C free-air temperature

PARAMETER	TEST CONDITIONS	2N200			UNIT
		MIN	TYP	MAX	
BV_{CBO} Collector-Base Breakdown Voltage	$I_C = 100 \mu a, I_E = 0$	25			v
BV_{EBO} Emitter-Base Breakdown Voltage	$I_E = 100 \mu a, I_C = 0$	25			v
$^*V_{PT}$ Punch Through Voltage†	$V_{EBF} = 1 v$	25			v
$^*I_{CBO}$ Collector Cutoff Current	$V_{CB} = 25 v, I_E = 0$		3	50	μa
$^*I_{EBO}$ Emitter Cutoff Current	$V_{EB} = 25 v, I_C = 0$		2	50	μa
$^*h_{FE}$ Static Forward Current Transfer Ratio	$V_{CE} = 1 v, I_C = 10 ma$	20	100		
	$V_{CE} = 0.35 v, I_C = 200 ma$	10	100		
$^*V_{BE}$ Base-Emitter Voltage	$I_B = 0.5 ma, I_C = 10 ma$	0.15	0.22	0.40	v
$^*V_{CE(sat)}$ Collector-Emitter Saturation Voltage	$I_B = 0.5 ma, I_C = 10 ma$		0.07	0.20	v
	$I_B = 0.25 ma, I_C = 10 ma$				v
	$I_B = 0.17 ma, I_C = 10 ma$				v
	$I_B = 0.13 ma, I_C = 10 ma$				v